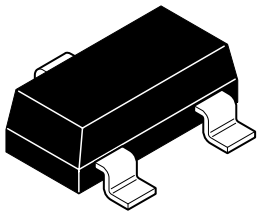
ZXTN25040DFH
40V, SOT23, NPN medium power transistor

Summary



BV_{CEX} > 130V

BV_{CEO} > 40V

BV_{ECO} > 6V

$I_{C(cont)}$ = 4A

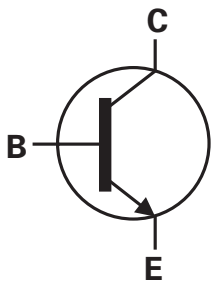
$V_{CE(sat)}$ < 55 mV @ 1A

$R_{CE(sat)}$ = 35 mΩ

P_D = 1.25W

Complementary part number ZXTP25040DFH

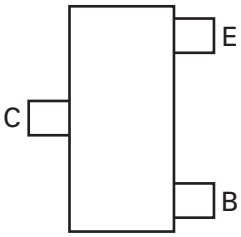
Description



Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

Features

- High power dissipation SOT23 package
- High peak current
- High gain
- Low saturation voltage
- 130V forward blocking voltage
- 6V reverse blocking voltage



Pinout - top view

Applications

- MOSFET gate drivers
- Power switches
- Motor control
- DC fans
- DC-DC converters

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25040DFHTA	7	8	3,000

Device marking

1A4

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	130	V
Collector-emitter voltage (forward blocking)	V_{CEX}	130	V
Collector-emitter voltage	V_{CEO}	40	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	6	V
Emitter-base voltage	V_{EBO}	7	V
Continuous collector current[c]	I_C	4	A
Base current	I_B	1	A
Peak pulse current	I_{CM}	10	A
Power dissipation at T_{amb} = 25°C[a]	P	0.73	W
Linear derating factor		5.84	mW/°C
Power dissipation at T_{amb} = 25°C[b]	P_D	1.05	W
Linear derating factor		8.4	mW/°C
Power dissipation at T_{amb} = 25°C[c]	P_D	1.25	W
Linear derating factor		9.6	mW/°C
Power dissipation at T_{amb} = 25°C[d]	P_D	1.81	W
Linear derating factor		14.5	mW/°C
Operating and storage temperature range	T_j, T_{stg}	- 55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient[a]	$R_{\Theta JA}$	171	°C/W
Junction to ambient[b]	$R_{\Theta JA}$	119	°C/W
Junction to ambient[c]	$R_{\Theta JA}$	100	°C/W
Junction to ambient[d]	$R_{\Theta JA}$	69	°C/W

NOTES:

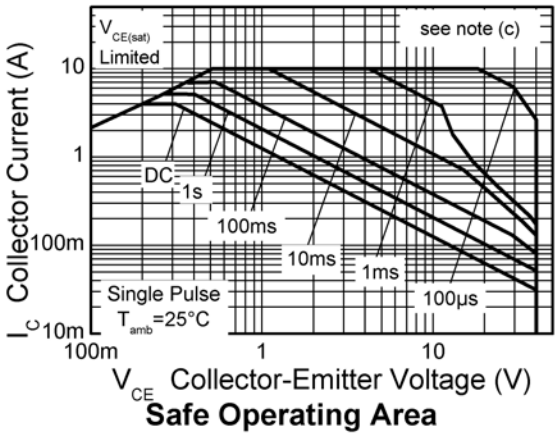
(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

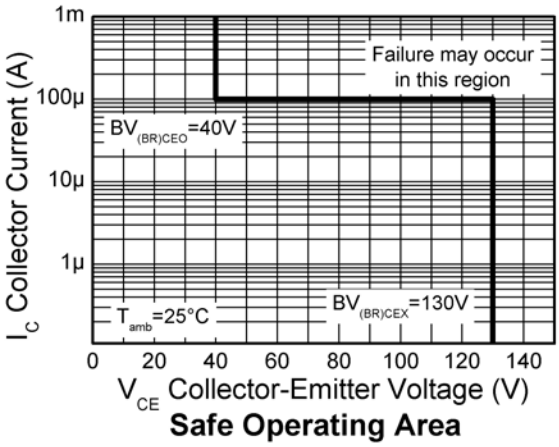
(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at t<5secs.

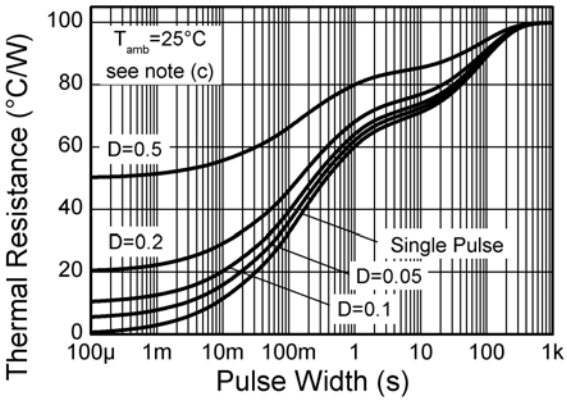
Characteristics



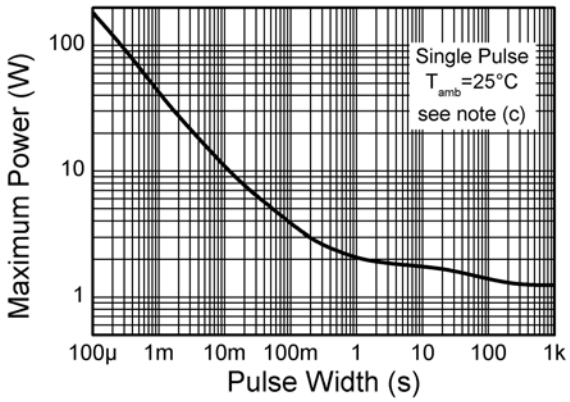
Safe Operating Area



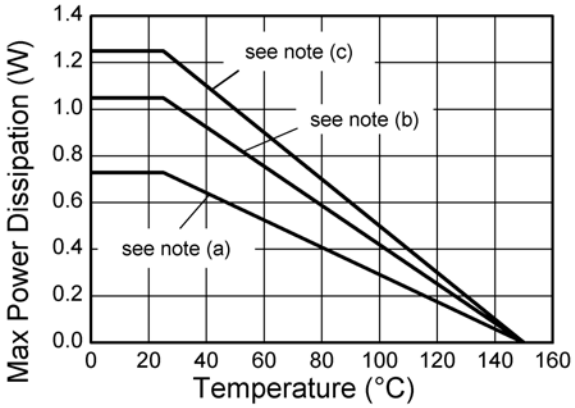
Safe Operating Area



Transient Thermal Impedance



Pulse Power Dissipation



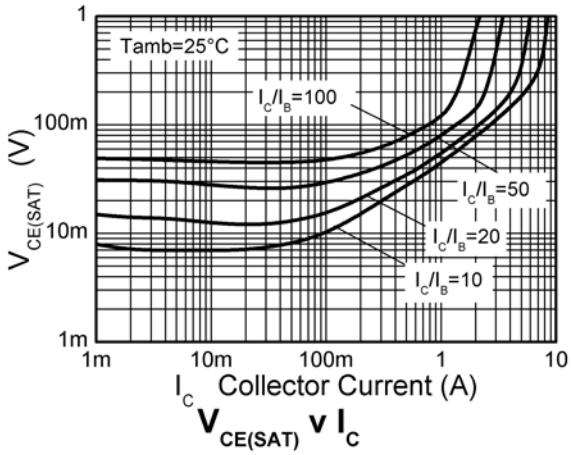
Derating Curve

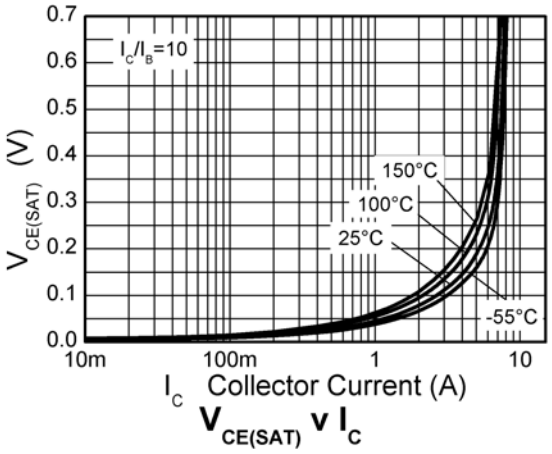
Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

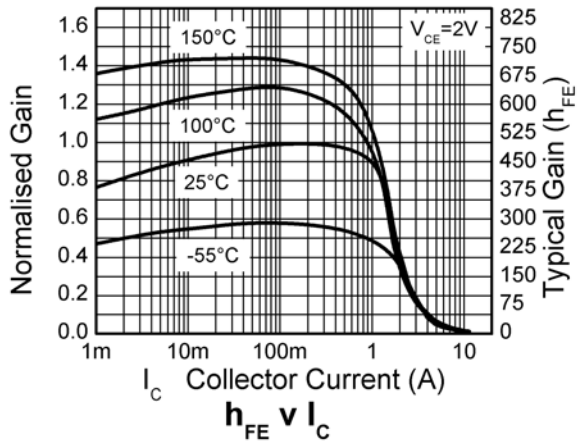
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	130	170		V	I_C = 100μA
Collector-emitter breakdown voltage (forward blocking)	BV_{CEX}	130	170		V	I_C = 100μA; R_{BE} < 1kΩ or -1V < V_{BE} < 0.25V
Collector-emitter breakdown voltage (base open)	BV_{CEO}	40	63		V	I_C = 10mA (*)
Emitter-base breakdown voltage	BV_{EBO}	7	8.3		V	I_E = 100μA
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	6	7.4		V	I_E = 100μA, R_{BC} < 1kΩ or 0.25V > V_{BC} > -0.25V
Emitter-collector breakdown voltage (base open)	BV_{ECO}	6	7.4		V	I_E = 100μA,
Collector-base cut-off current	I_{CBO}		<1	50 20	nA μA	V_{CB} = 100V V_{CB} = 100V, T_{amb}= 100°C
Collector-emitter cut-off current	I_{CEX}		-	100	nA	V_{CE} = 100V; R_{BE} < 1kΩ or -1V < V_{BE} < 0.25V
Emitter-base cut-off current	I_{EBO}		<1	50	nA	V_{EB} = 5.6V
Collector-emitter saturation voltage	$V_{CE(sat)}$		45 120 135 140	55 210 210 190	mV mV mV mV	I_C = 1A, I_B = 100mA(*) I_C = 1A, I_B = 10mA(*) I_C = 2A, I_B = 40mA(*) I_C = 4A, I_B = 400mA(*)
Base-emitter saturation voltage	$V_{BE(sat)}$		960	1050	mV	I_C = 4A, I_B = 400mA(*)
Base-emitter turn-on voltage	$V_{BE(on)}$		840	950	mV	I_C = 4A, V_{CE} = 2V(*)
Static forward current transfer ratio	h_{FE}	300 300 30	450 450 60 10	900		I_C = 10mA, V_{CE} = 2V(*) I_C = 1A, V_{CE} = 2V(*) I_C = 4A, V_{CE} = 2V(*) I_C = 10A, V_{CE} = 2V(*)
Transition frequency	f_T		190		MHz	I_C = 50mA, V_{CE} = 10V f = 100MHz
Output capacitance	C_{OBO}		11.7	20	pF	V_{CB} = 10V, f = 1MHz(*)
Delay time	t_d		64		ns	V_{CC} = 10V, I_C = 1A, I_{B1} = I_{B2}= 10mA
Rise time	t_r		108		ns	
Storage time	t_s		428		ns	
Fall time	t_f		130		ns	

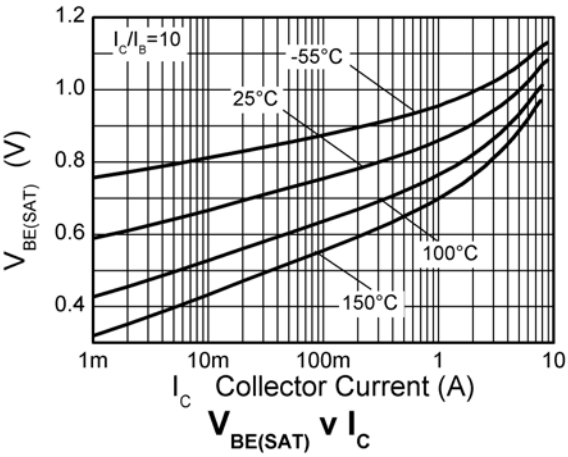
NOTES:
(*) Measured under pulsed conditions. Pulse width ≤300μs; duty cycle ≤2%.

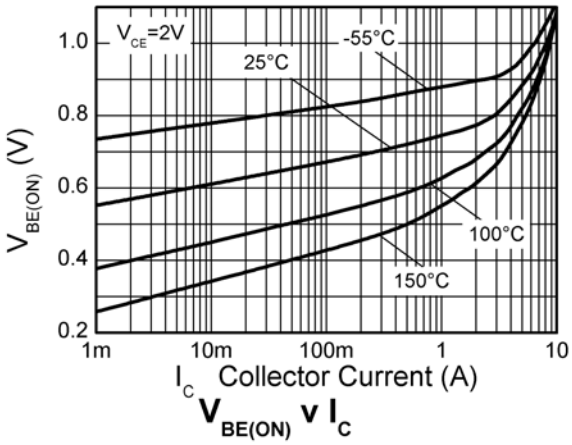
Typical characteristics



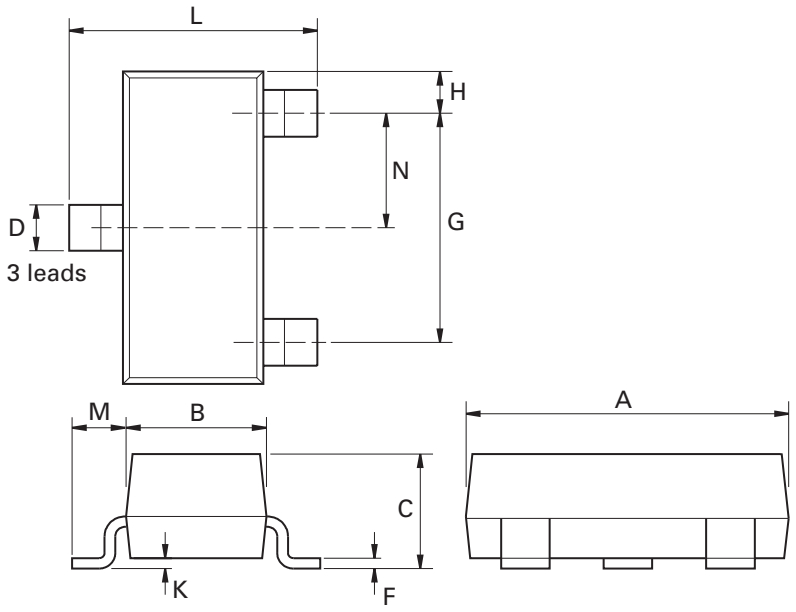








Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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